

Title (en)

METHOD OF FORMING BOTTOM ELECTRODES FOR USE WITH METAL OXIDE RESISTIVITY SWITCHING LAYERS

Title (de)

VERFAHREN ZUR HERSTELLUNG VON BODENELEKTRODEN ZUR VERWENDUNG MIT METALLOXIDWIDERSTANDSSCHALTSCHICHTEN

Title (fr)

PROCÉDÉ DE FABRICATION D'ÉLECTRODES INFÉRIEURES POUR UNE UTILISATION AVEC DES COUCHES À COMMUTATION DE RÉSISTIVITÉ D'OXYDE MÉTALLIQUE

Publication

**EP 2548238 A1 20130123 (EN)**

Application

**EP 11712085 A 20110314**

Priority

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Abstract (en)

[origin: US2011227020A1] In a first aspect, a metal-insulator-metal (MIM) stack is provided that includes (1) a first conductive layer comprising a silicon-germanium (SiGe) alloy; (2) a resistivity-switching layer comprising a metal oxide layer formed above the first conductive layer; and (3) a second conductive layer formed above the resistivity-switching layer. A memory cell may be formed from the MIM stack. Numerous other aspects are provided.

IPC 8 full level

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CPC (source: EP KR US)

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